

# Mikael stling

## List of Publications by Citations

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396  
papers

7,442  
citations

40  
h-index

69  
g-index

430  
ext. papers

8,439  
ext. citations

3.2  
avg, IF

5.91  
L-index

#	Paper	IF	Citations
396	Efficient inkjet printing of graphene. <i>Advanced Materials</i> , <b>2013</b> , 25, 3985-92	24	375
395	Metal Silicides in CMOS Technology: Past, Present, and Future Trends. <i>Critical Reviews in Solid State and Materials Sciences</i> , <b>2003</b> , 28, 1-129	10.1	280
394	Electromechanical piezoresistive sensing in suspended graphene membranes. <i>Nano Letters</i> , <b>2013</b> , 13, 3237-42	11.5	261
393	Residual metallic contamination of transferred chemical vapor deposited graphene. <i>ACS Nano</i> , <b>2015</b> , 9, 4776-85	16.7	210
392	Scalable Fabrication and Integration of Graphene Microsupercapacitors through Full Inkjet Printing. <i>ACS Nano</i> , <b>2017</b> , 11, 8249-8256	16.7	204
391	Resistive graphene humidity sensors with rapid and direct electrical readout. <i>Nanoscale</i> , <b>2015</b> , 7, 19099-109	10.9	194
390	A graphene-based hot electron transistor. <i>Nano Letters</i> , <b>2013</b> , 13, 1435-9	11.5	181
389	Inkjet Printing of MoS <sub>2</sub> . <i>Advanced Functional Materials</i> , <b>2014</b> , 24, 6524-6531	15.6	167
388	<b>2011</b> ,		149
387	Vertical Graphene Base Transistor. <i>IEEE Electron Device Letters</i> , <b>2012</b> , 33, 691-693	4.4	129
386	Inkjet printed highly transparent and flexible graphene micro-supercapacitors. <i>Nanoscale</i> , <b>2017</b> , 9, 6998-7005	10.9	101
385	Enhanced formation of the C54 phase of TiSi <sub>2</sub> by an interposed layer of molybdenum. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 975-977	3.4	85
384	Schottky-Barrier Height Tuning by Means of Ion Implantation Into Preformed Silicide Films Followed by Drive-In Anneal. <i>IEEE Electron Device Letters</i> , <b>2007</b> , 28, 565-568	4.4	82
383	. <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 396-403	2.9	80
382	Prevention of Graphene Restacking for Performance Boost of Supercapacitors: A Review. <i>Crystals</i> , <b>2013</b> , 3, 163-190	2.3	78
381	A comparative study of the diffusion barrier properties of TiN and ZrN. <i>Thin Solid Films</i> , <b>1986</b> , 145, 81-88	2.2	78
380	Piezoresistive Properties of Suspended Graphene Membranes under Uniaxial and Biaxial Strain in Nanoelectromechanical Pressure Sensors. <i>ACS Nano</i> , <b>2016</b> , 10, 9879-9886	16.7	77

379	Inkjet printing of 2D layered materials. <i>ChemPhysChem</i> , <b>2014</b> , 15, 3427-34	3.2	69
378	. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 1199-1206	2.9	69
377	. <i>IEEE Electron Device Letters</i> , <b>2013</b> , 34, 1091-1093	4.4	66
376	Reduction of the Schottky barrier height on silicon carbide using Au nano-particles. <i>Solid-State Electronics</i> , <b>2002</b> , 46, 1433-1440	1.7	64
375	. <i>IEEE Transactions on Electron Devices</i> , <b>2002</b> , 49, 514-520	2.9	61
374	Chemical vapor deposited graphene: From synthesis to applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 2439-2449	1.6	59
373	Investigation of aluminum nitride grown by metalloorganic chemical-vapor deposition on silicon carbide. <i>Journal of Applied Physics</i> , <b>1997</b> , 82, 2990-2995	2.5	55
372	Pressure sensors based on suspended graphene membranes. <i>Solid-State Electronics</i> , <b>2013</b> , 88, 89-94	1.7	54
371	Thermally stable low ohmic contacts to p-type 6H-SiC using cobalt silicides. <i>Solid-State Electronics</i> , <b>1996</b> , 39, 1559-1565	1.7	54
370	All-solid-state micro-supercapacitors based on inkjet printed graphene electrodes. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 123901	3.4	53
369	Surface-Passivation Effects on the Performance of 4H-SiC BJTs. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 259-265	2.9	50
368	Geometrical effects in high current gain 1100-V 4H-SiC BJTs. <i>IEEE Electron Device Letters</i> , <b>2005</b> , 26, 743-745	4.4	50
367	Graphene-based CO <sub>2</sub> sensing and its cross-sensitivity with humidity. <i>RSC Advances</i> , <b>2017</b> , 7, 22329-22339	3.7	49
366	Modeling and Characterization of Current Gain Versus Temperature in 4H-SiC Power BJTs. <i>IEEE Transactions on Electron Devices</i> , <b>2010</b> , 57, 704-711	2.9	49
365	. <i>IEEE Transactions on Electron Devices</i> , <b>2012</b> , 59, 1076-1083	2.9	46
364	Ultradeep, low-damage dry etching of SiC. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 739-741	3.4	45
363	High-Voltage 4H-SiC PiN Diodes With Etched Junction Termination Extension. <i>IEEE Electron Device Letters</i> , <b>2009</b> , 30, 1170-1172	4.4	44
362	Low resistivity ohmic titanium carbide contacts to n- and p-type 4H-silicon carbide. <i>Solid-State Electronics</i> , <b>2000</b> , 44, 1179-1186	1.7	43

- 361 Humidity and CO<sub>2</sub> gas sensing properties of double-layer graphene. *Carbon*, **2018**, 127, 576-587 10.4 43
- 360 A simple route towards high-concentration surfactant-free graphene dispersions. *Carbon*, **2012**, 50, 3113-3116 4.2
- 359 1200-V 5.2- $\Omega$ cm<sup>2</sup> 4H-SiC BJTs With a High Common-Emitter Current Gain. *IEEE Electron Device Letters*, **2007**, 28, 1007-1009 4.4 42
- 358 Bilayer insulator tunnel barriers for graphene-based vertical hot-electron transistors. *Nanoscale*, **2015**, 7, 13096-104 7.7 40
- 357 ICP etching of SiC. *Solid-State Electronics*, **1998**, 42, 2283-2288 1.7 40
- 356 Schottky diode formation and characterization of titanium tungsten to n- and p-type 4H silicon carbide. *Journal of Applied Physics*, **2000**, 87, 8039-8044 2.5 40
- 355 Graphene ribbons with suspended masses as transducers in ultra-small nanoelectromechanical accelerometers. *Nature Electronics*, **2019**, 2, 394-404 28.4 38
- 354 Fully inkjet printed ultrathin microsupercapacitors based on graphene electrodes and a nano-graphene oxide electrolyte. *Nanoscale*, **2019**, 11, 10172-10177 7.7 37
- 353 Percolation thresholds of two-dimensional continuum systems of rectangles. *Physical Review E*, **2013**, 88, 012101 2.4 37
- 352 1/f noise in Si and Si/sub 0.7/Ge/sub 0.3/ pMOSFETs. *IEEE Transactions on Electron Devices*, **2003**, 50, 2513-2519 3.7
- 351 Schottky barrier height dependence on the metal work function for p-type 4H-silicon carbide. *Journal of Electronic Materials*, **2001**, 30, 242-246 1.9 36
- 350 Going ballistic: Graphene hot electron transistors. *Solid State Communications*, **2015**, 224, 64-75 1.6 34
- 349 Thin-film growth and compositional effects in YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7-x</sub> layers prepared by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **1993**, 74, 4631-4642 2.5 34
- 348 Morphological instabilities of nickel and cobalt silicides on silicon. *Applied Surface Science*, **1991**, 53, 87-96.7 33
- 347 SB-MOSFETs in UTB-SOI Featuring PtSi Source/Drain With Dopant Segregation. *IEEE Electron Device Letters*, **2008**, 29, 125-127 4.4 32
- 346 Comprehensive study on low-frequency noise and mobility in Si and SiGe pMOSFETs with high- $\kappa$ /gate dielectrics and TiN gate. *IEEE Transactions on Electron Devices*, **2006**, 53, 836-843 2.9 32
- 345 Formation and characterization of cobalt 6H-silicon carbide Schottky contacts. *Applied Physics Letters*, **1993**, 63, 3069-3071 3.4 32
- 344 15 kV-Class Implantation-Free 4H-SiC BJTs With Record High Current Gain. *IEEE Electron Device Letters*, **2018**, 39, 63-66 4.4 30

343	Lateral encroachment of Ni-silicides in the source/drain regions on ultrathin silicon-on-insulator. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 253507	3.4	30
342	Via-hole etching for SiC. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1999</b> , 17, 2050		30
341	Temperature stability of cobalt Schottky contacts on n- and p-type 6H silicon carbide. <i>Applied Surface Science</i> , <b>1993</b> , 73, 316-321	6.7	30
340	Bias-temperature instability in single-layer graphene field-effect transistors. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 143507	3.4	29
339	2.2 kV SiC BJTs with Low VCESAT Fast Switching and Short-Circuit Capability. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 1033-1036	0.4	29
338	Influence of growth conditions on electrical characteristics of AlN on SiC. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 3549-3551	3.4	29
337	Limitation of Ti/TiN diffusion barrier layers in silicon technology. <i>Vacuum</i> , <b>1985</b> , 35, 547-553	3.7	29
336	Graphene transfer methods for the fabrication of membrane-based NEMS devices. <i>Microelectronic Engineering</i> , <b>2016</b> , 159, 108-113	2.5	29
335	Fabrication of 2700-V $12\text{-}\Omega\cdot\text{cm}^2$ Non Ion-Implanted 4H-SiC BJTs With Common-Emitter Current Gain of 50. <i>IEEE Electron Device Letters</i> , <b>2008</b> , 29, 1135-1137	4.4	28
334	Reduced self-heating by strained silicon substrate engineering. <i>Applied Surface Science</i> , <b>2008</b> , 254, 6182-6185	6.1	28
333	Low resistivity ohmic contacts on 4H-silicon carbide for high power and high temperature device applications. <i>Microelectronic Engineering</i> , <b>2002</b> , 60, 261-268	2.5	27
332	Electrical characterization of TiC ohmic contacts to aluminum ion implanted 4H-silicon carbide. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 1478-1480	3.4	27
331	CVD-based tungsten carbide schottky contacts to 6H-SiC for very high-temperature operation. <i>Journal of Electronic Materials</i> , <b>2000</b> , 29, 372-375	1.9	27
330	Plasma chemistries for high density plasma etching of SiC. <i>Journal of Electronic Materials</i> , <b>1999</b> , 28, 196-201	6.1	26
329	CoSi <sub>2</sub> ohmic contacts to n-type 6H-SiC. <i>Solid-State Electronics</i> , <b>1995</b> , 38, 2023-2028	1.7	26
328	TiSi <sub>2</sub> /TiN Stable Multilayered Contact Structure for Shallow Implanted Junctions in VLSI Technology. <i>Physica Scripta</i> , <b>1983</b> , 28, 633-636	2.6	26
327	A robust spacer gate process for deca-nanometer high-frequency MOSFETs. <i>Microelectronic Engineering</i> , <b>2006</b> , 83, 434-439	2.5	25
326	Dependence of the colored frequency noise in spin torque oscillators on current and magnetic field. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 092405	3.4	24

325	High-Voltage (2.8 kV) Implantation-Free 4H-SiC BJTs With Long-Term Stability of the Current Gain. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 2665-2669	2.9	24
324	Interaction of NiSi with dopants for metallic source/drain applications. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2010</b> , 28, C111-C1111	1.3	24
323	Surface passivation oxide effects on the current gain of 4H-SiC bipolar junction transistors. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 082113	3.4	23
322	Fabrication and characterization of heterojunction diodes with HVPE-grown GaN on 4H-SiC. <i>IEEE Transactions on Electron Devices</i> , <b>2001</b> , 48, 444-449	2.9	23
321	Formation of iron disilicide on amorphous silicon. <i>Applied Surface Science</i> , <b>1991</b> , 53, 153-158	6.7	23
320	Arsenic distribution in bilayers of TiSi <sub>2</sub> on polycrystalline silicon during heat treatment. <i>Thin Solid Films</i> , <b>1983</b> , 110, 281-289	2.2	23
319	Optimizing the optical and electrical properties of graphene ink thin films by laser-annealing. <i>2D Materials</i> , <b>2015</b> , 2, 011003	5.9	22
318	5.8-kV Implantation-Free 4H-SiC BJT With Multiple-Shallow-Trench Junction Termination Extension. <i>IEEE Electron Device Letters</i> , <b>2015</b> , 36, 168-170	4.4	22
317	Effects of Carbon on Schottky Barrier Heights of NiSi Modified by Dopant Segregation. <i>IEEE Electron Device Letters</i> , <b>2009</b> , 30, 608-610	4.4	22
316	Influence of Emitter Width and Emitter-Base Distance on the Current Gain in 4H-SiC Power BJTs. <i>IEEE Transactions on Electron Devices</i> , <b>2010</b> , 57, 2664-2670	2.9	22
315	A novel strained Si/sub 0.7/Ge/sub 0.3/ surface-channel pMOSFET with an ALD TiN/Al/sub 2/O/sub 3//HfAlO/sub x//Al/sub 2/O <sub>3</sub> gate stack. <i>IEEE Electron Device Letters</i> , <b>2003</b> , 24, 171-173	4.4	22
314	Bipolar integrated circuits in SiC for extreme environment operation. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 034002	1.8	21
313	High rate etching of SiC and SiCN in NF <sub>3</sub> inductively coupled plasmas. <i>Solid-State Electronics</i> , <b>1998</b> , 42, 743-747	1.7	21
312	Stable dynamic avalanche in Si power diodes. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 3170-3172	3.4	21
311	Nickel-enhanced solid-phase epitaxial regrowth of amorphous silicon. <i>Physical Review Letters</i> , <b>1992</b> , 68, 1872-1875	7.4	21
310	Hot-Carrier Degradation and Bias-Temperature Instability in Single-Layer Graphene Field-Effect Transistors: Similarities and Differences. <i>IEEE Transactions on Electron Devices</i> , <b>2015</b> , 62, 3876-3881	2.9	20
309	Influence of Passivation Oxide Thickness and Device Layout on the Current Gain of SiC BJTs. <i>IEEE Electron Device Letters</i> , <b>2015</b> , 36, 11-13	4.4	20
308	A manufacturable process integration approach for graphene devices. <i>Solid-State Electronics</i> , <b>2013</b> , 84, 185-190	1.7	20

307	Impact of strain and channel orientation on the low-frequency noise performance of Si n- and pMOSFETs. <i>Solid-State Electronics</i> , <b>2007</b> , 51, 771-777	1.7	20
306	High-resolution recoil spectrometry for separate characterization of Ga and As in Al <sub>x</sub> Ga(1-x)As structures. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 219-221	3.4	20
305	550 °C 4H-SiC p-i-n Photodiode Array With Two-Layer Metallization. <i>IEEE Electron Device Letters</i> , <b>2016</b> , 37, 1594-1596	4.4	19
304	Scalable Fabrication of 2D Semiconducting Crystals for Future Electronics. <i>Electronics (Switzerland)</i> , <b>2015</b> , 4, 1033-1061	2.6	19
303	Strained Si/SiGe MOS technology: Improving gate dielectric integrity. <i>Microelectronic Engineering</i> , <b>2009</b> , 86, 218-223	2.5	19
302	New method to calibrate the pattern dependency of selective epitaxy of SiGe layers. <i>Solid-State Electronics</i> , <b>2009</b> , 53, 858-861	1.7	19
301	Robust, scalable self-aligned platinum silicide process. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 142114	3.4	19
300	Carrier transport through a dry-etched InP-based two-dimensional photonic crystal. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 123101	2.5	19
299	Ferroelectric Pb(Zr <sub>0.52</sub> Ti <sub>0.48</sub> )/SiC field-effect transistor. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 3975-3977	3.4	19
298	Inductively coupled plasma etch damage in 4H-SiC investigated by Schottky diode characterization. <i>Journal of Electronic Materials</i> , <b>2001</b> , 30, 247-252	1.9	19
297	Reactive sputtering of titanium boride. <i>Thin Solid Films</i> , <b>1989</b> , 172, 133-140	2.2	19
296	Suspended Graphene Membranes with Attached Silicon Proof Masses as Piezoresistive Nanoelectromechanical Systems Accelerometers. <i>Nano Letters</i> , <b>2019</b> , 19, 6788-6799	11.5	18
295	Ink-jet printed thin-film transistors with carbon nanotube channels shaped in long strips. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 084915	2.5	18
294	. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 2081-2087	2.9	18
293	RF Performance Projections of Graphene FETs vs. Silicon MOSFETs. <i>ECS Solid State Letters</i> , <b>2012</b> , 1, Q39-Q41		18
292	Performance Fluctuation of FinFETs With Schottky Barrier Source/Drain. <i>IEEE Electron Device Letters</i> , <b>2008</b> , 29, 506-508	4.4	18
291	Characterization of heterojunction diodes with hydride vapor phase epitaxy grown AlGa <sub>n</sub> on 4H-SiC. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 2372-2379	2.5	18
290	Silicon nitride films deposited from SiH <sub>2</sub> Cl <sub>2</sub> ?NH <sub>3</sub> by low pressure chemical vapor deposition: kinetics, thermodynamics, composition and structure. <i>Thin Solid Films</i> , <b>1992</b> , 213, 182-191	2.2	18

289	Wet Transfer of Inkjet Printed Graphene for Microsupercapacitors on Arbitrary Substrates. <i>ACS Applied Energy Materials</i> , <b>2019</b> , 2, 158-163	6.1	18
288	Manufacture and characterization of graphene membranes with suspended silicon proof masses for MEMS and NEMS applications. <i>Microsystems and Nanoengineering</i> , <b>2020</b> , 6, 17	7.7	18
287	Large scale integration of graphene transistors for potential applications in the back end of the line. <i>Solid-State Electronics</i> , <b>2015</b> , 108, 61-66	1.7	17
286	SiC Etching and Sacrificial Oxidation Effects on the Performance of 4H-SiC BJTs. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 1005-1008	0.4	17
285	Low-Temperature Annealing of Radiation-Induced Degradation in 4H-SiC Bipolar Junction Transistors. <i>IEEE Electron Device Letters</i> , <b>2010</b> , 31, 707-709	4.4	17
284	The performance improvement evaluation for SiGe-based IR detectors. <i>Solid-State Electronics</i> , <b>2011</b> , 62, 72-76	1.7	17
283	Threshold of hierarchical percolating systems. <i>Physical Review E</i> , <b>2012</b> , 85, 021109	2.4	17
282	High-Current-Gain SiC BJTs With Regrown Extrinsic Base and Etched JTE. <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 1894-1898	2.9	17
281	Self-heating effects in a BiCMOS on SOI technology for RFIC applications. <i>IEEE Transactions on Electron Devices</i> , <b>2005</b> , 52, 1423-1428	2.9	17
280	Dynamic avalanche in 3.3-kV Si power diodes. <i>IEEE Transactions on Electron Devices</i> , <b>1999</b> , 46, 781-786	2.9	17
279	Thermal degradation of TiSi <sub>2</sub> /poly-Si gate electrodes. <i>Thin Solid Films</i> , <b>1989</b> , 168, 325-334	2.2	17
278	Precise percolation thresholds of two-dimensional random systems comprising overlapping ellipses. <i>Physica A: Statistical Mechanics and Its Applications</i> , <b>2016</b> , 462, 940-950	3.3	17
277	On the electron mobility enhancement in biaxially strained Si MOSFETs. <i>Solid-State Electronics</i> , <b>2008</b> , 52, 498-505	1.7	16
276	Low-frequency noise and Coulomb scattering in Si <sub>0.8</sub> Ge <sub>0.2</sub> surface channel pMOSFETs with ALD Al <sub>2</sub> O <sub>3</sub> gate dielectrics. <i>Solid-State Electronics</i> , <b>2005</b> , 49, 907-914	1.7	16
275	Random telegraph signal noise in SiGe heterojunction bipolar transistors. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 4414-4421	2.5	16
274	Chemical vapor deposition of undoped and in-situ boron- and arsenic-doped epitaxial and polycrystalline silicon films grown using silane at reduced pressure. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 1655-1663	2.5	16
273	Modeling the variation of the low-frequency noise in polysilicon emitter bipolar junction transistors. <i>IEEE Electron Device Letters</i> , <b>2001</b> , 22, 242-244	4.4	16
272	Rapid thermal annealing induced reactions of Co/GaAs thin film structures: Studies using mass and energy dispersive recoil spectrometry. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 835-843	2.5	16



271	Thulium Silicate Interfacial Layer for Scalable High-k/Metal Gate Stacks. <i>IEEE Transactions on Electron Devices</i> , <b>2013</b> , 60, 3271-3276	2.9	15
270	On Different Process Schemes for MOSFETs With a Controllable NiSi-Based Metallic Source/Drain. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 1898-1906	2.9	15
269	Fully Depleted UTB and Trigate N-Channel MOSFETs Featuring Low-Temperature PtSi Schottky-Barrier Contacts With Dopant Segregation. <i>IEEE Electron Device Letters</i> , <b>2009</b> , 30, 541-543	4.4	15
268	A Hysteresis-Free High-k Dielectric and Contact Resistance Considerations for Graphene Field Effect Transistors. <i>ECS Transactions</i> , <b>2011</b> , 41, 165-171	1	15
267	Ferroelectric thin films on silicon carbide for next-generation nonvolatile memory and sensor devices. <i>Thin Solid Films</i> , <b>2004</b> , 469-470, 444-449	2.2	15
266	The influence of band offsets on the IV characteristics for GaN/SiC heterojunctions. <i>Solid-State Electronics</i> , <b>2002</b> , 46, 827-835	1.7	15
265	A low-complexity 62-GHz FT SiGe heterojunction bipolar transistor process using differential epitaxy and in situ phosphorus-doped poly-Si emitter at very low thermal budget. <i>Solid-State Electronics</i> , <b>2000</b> , 44, 549-554	1.7	15
264	Influence of the addition of Co and Ni on the formation of epitaxial semiconducting $\text{FeSi}_2$ : Comparison of different evaporation methods. <i>Journal of Applied Physics</i> , <b>1998</b> , 83, 4193-4201	2.5	15
263	Effect of annealing on SiC thin films prepared by pulsed laser deposition. <i>Diamond and Related Materials</i> , <b>1999</b> , 8, 2099-2102	3.5	15
262	A quantitative study of oxygen behavior during $\text{CrSi}_2$ and $\text{TiSi}_2$ formation. <i>Journal of Applied Physics</i> , <b>1989</b> , 65, 567-574	2.5	15
261	Noninvasive Scanning Raman Spectroscopy and Tomography for Graphene Membrane Characterization. <i>Nano Letters</i> , <b>2017</b> , 17, 1504-1511	11.5	14
260	Conductivity modulated on-axis 4H-SiC 10+ kV PiN diodes <b>2015</b> ,		14
259	. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 1-1	4.4	14
258	Strain Engineering in GeSnSi Materials. <i>ECS Transactions</i> , <b>2013</b> , 50, 527-531	1	14
257	High power devices in wide bandgap semiconductors. <i>Science China Information Sciences</i> , <b>2011</b> , 54, 1087-1093	3.1	14
256	A novel self-aligned process for platinum silicide nanowires. <i>Microelectronic Engineering</i> , <b>2006</b> , 83, 2107-2111	2.5	14
255	Control of Self-Heating in Thin Virtual Substrate Strained Si MOSFETs. <i>IEEE Transactions on Electron Devices</i> , <b>2006</b> , 53, 2296-2305	2.9	14
254	Low-frequency noise in $\text{Si}_{0.7}\text{Ge}_{0.3}$ surface channel pMOSFETs with ALD $\text{HfO}_2/\text{Al}_2\text{O}_3$ gate dielectrics. <i>Solid-State Electronics</i> , <b>2004</b> , 48, 2271-2275	1.7	14

253	Extraction of emitter and base series resistances of bipolar transistors from a single DC measurement. <i>IEEE Transactions on Semiconductor Manufacturing</i> , <b>2000</b> , 13, 119-126	2.6	14
252	Preparation of AlN thin films by nitridation of Al-coated Si substrate. <i>Thin Solid Films</i> , <b>1999</b> , 340, 137-139	2.2	14
251	Conductivity scaling in supercritical percolation of nanoparticles--not a power law. <i>Nanoscale</i> , <b>2015</b> , 7, 3424-8	7.7	13
250	Effects of carbon pre-silicidation implant into Si substrate on NiSi. <i>Microelectronic Engineering</i> , <b>2014</b> , 120, 178-181	2.5	13
249	500 °C High Current 4H-SiC Lateral BJTs for High-Temperature Integrated Circuits. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 1429-1432	4.4	13
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100	. <i>IEEE Transactions on Electron Devices</i> , <b>2012</b> , 59, 1585-1591	2.9	3
99	Direct birefringence and transmission modulation via dynamic alignment of P3HT nanofibers in an advanced opto-fluidic component. <i>Optical Materials Express</i> , <b>2017</b> , 7, 52	2.6	3
98	Characterization of SiGe/Si multi-quantum wells for infrared sensing. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 251609	3.4	3
97	SiC Bipolar Power Transistors - Design and Technology Issues for Ultimate Performance. <i>Materials Research Society Symposia Proceedings</i> , <b>2010</b> , 1246, 1		3
96	Quantifying hole mobility degradation in pMOSFETs with a strained-Si <sub>0.7</sub> Ge <sub>0.3</sub> surface-channel under an ALD TiN/Al <sub>2</sub> O <sub>3</sub> /HfAlO <sub>x</sub> /Al <sub>2</sub> O <sub>3</sub> gate stack. <i>Solid-State Electronics</i> , <b>2004</b> , 48, 721-729	1.7	3
95	Lateral base design rules for optimized low-frequency noise of differentially grown SiGe heterojunction bipolar transistors. <i>Microelectronics Reliability</i> , <b>2001</b> , 41, 881-886	1.2	3
94	High Temperature Stable Titanium Carbide Ohmic and Schottky Contacts to SiC. <i>Materials Research Society Symposia Proceedings</i> , <b>1998</b> , 512, 125		3
93	Metal/InP thin film reactions: Studies using mass and energy dispersive recoil spectrometry. <i>Vacuum</i> , <b>1995</b> , 46, 737-738	3.7	3
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91	Observation of anomalous high resistance to implanted areas caused by reactive ion etching (RIE). <i>Vacuum</i> , <b>1988</b> , 38, 801-812	3.7	3
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88	Graphene- and 2D Material-Based Thin-Film Printing <b>2017</b> , 161-181		2
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83	Editorial Toward Faster Publishing and Shorter Turnaround Time. <i>IEEE Journal of the Electron Devices Society</i> , <b>2018</b> , 6, 1-1	2.3	2
82	Toward effective passivation of graphene to humidity sensing effects <b>2016</b> ,		2
81	Improved designs of Si-based quantum wells and Schottky diodes for IR detection. <i>Thin Solid Films</i> , <b>2016</b> , 613, 19-23	2.2	2
80	Effective workfunction control in TmSiO/HfO <sub>2</sub> high-k/metal gate stacks <b>2014</b> ,		2
79	Fabrication and characterization of silicon nanowires using STL for biosensing applications <b>2014</b> ,		2
78	Embedded graphene photodetectors for silicon photonics <b>2014</b> ,		2
77	Wafer scale graphene transfer for back end of the line device integration <b>2014</b> ,		2
76	Integration of Silicon Nanowires with CMOS <b>2014</b> , 65-72		2
75	Fabrication of Relaxed Germanium on Insulator via Room Temperature Wafer Bonding. <i>ECS Transactions</i> , <b>2014</b> , 64, 533-541	1	2
74	Silicon nanowires integrated in a fully depleted CMOS process for charge based biosensing <b>2013</b> ,		2

73	Bias-temperature instability in single-layer graphene field-effect transistors: A reliability challenge <b>2014</b> ,		2
72	Characterization of $\text{La}_x\text{Hf}_{1-x}\text{O}_3$ Gate Dielectrics in 4H-SiC MOS Capacitor. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 549-552	0.4	2
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67	Simulation of low Schottky barrier MOSFETs using an improved Multi-subband Monte Carlo model. <i>Solid-State Electronics</i> , <b>2013</b> , 79, 172-178	1.7	2
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47	Impact of hot carrier stress on the defect density and mobility in double-gated graphene field-effect transistors <b>2015</b> ,		1
46	Low-Frequency Noise Characterization of Ultra-Low Equivalent-Oxide-Thickness Thulium Silicate Interfacial Layer nMOSFETs. <i>IEEE Electron Device Letters</i> , <b>2015</b> , 36, 1355-1358	4.4	1
45	Characterization of bonding surface and electrical insulation properties of inter layer dielectrics for 3D monolithic integration <b>2015</b> ,		1
44	Sensitivity of the crystal quality of SiGe layers grown at low temperatures by trisilane and germane. <i>Thin Solid Films</i> , <b>2016</b> , 613, 38-42	2.2	1
43	Fabrication of strained Ge on insulator via room temperature wafer bonding <b>2014</b> ,		1
42	The impact of atomic layer depositions on high quality Ge/GeO <sub>2</sub> interfaces fabricated by rapid thermal annealing in O <sub>2</sub> ambient <b>2017</b> ,		1
41	Hot-carrier degradation in single-layer double-gated graphene field-effect transistors <b>2015</b> ,		1
40	Graphene-based piezoresistive pressure sensing for uniaxial and biaxial strains <b>2014</b> ,		1
39	Recent advances in high-k dielectrics and inter layer engineering <b>2014</b> ,		1
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27	Effect of anisotropic material properties on the forward voltage drop in 6H- and 4H-SiC power diode structures. <i>Semiconductor Science and Technology</i> , <b>1999</b> , 14, 125-129	1.8	1
26	TiSi <sub>2</sub> Phase Transformation by Amorphization Techniques. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 441, 283		1
25	Studies of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> formation in coevaporated Y <sub>2</sub> BaF <sub>2</sub> Cu <sub>2</sub> O thin films on sapphire substrates. <i>Thin Solid Films</i> , <b>1994</b> , 247, 213-225	2.2	1
24	Formation of Nickel Silicides on Ion-Amorphized Silicon. <i>Materials Research Society Symposia Proceedings</i> , <b>1992</b> , 260, 405		1
23	In-Situ Preparation of Y-Ba-Cu-O Thin Films Using Mass-Spectrometer Rate Control and Atomic Oxygen. <i>Materials Research Society Symposia Proceedings</i> , <b>1992</b> , 275, 299		1
22	(Invited) Emerging Graphene Device Technologies. <i>ECS Transactions</i> , <b>2016</b> , 75, 17-35	1	1
21	4H-SiC pMOSFETs with Al-Doped S/D and NbNi Silicide Ohmic Contacts. <i>Materials Science Forum</i> , <b>2018</b> , 924, 423-427	0.4	1
20	Device design for a raised extrinsic base SiGe bipolar technology. <i>Solid-State Electronics</i> , <b>2004</b> , 48, 1927-1931	0	0

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18	Hydrogen in undoped and heavily in situ phosphorus doped silicon films deposited using disilane and phosphine. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 1970-1973	2.5	0
17	Process Conditions for Low Interface State Density in Si-passivated Ge Devices with TmSiO Interfacial Layer. <i>ECS Journal of Solid State Science and Technology</i> , <b>2020</b> , 9, 125009	2	0
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6	Cobalt Silicide OHMIC Contacts to 6H-SiC. <i>Materials Research Society Symposia Proceedings</i> , <b>1994</b> , 339, 229		
5	Influence of standard processing on area-selective chemical vapour deposition of tungsten on tantalum disilicide. <i>Applied Surface Science</i> , <b>1991</b> , 53, 35-40	6.7	
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